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October 2013

FDP8N50NZ / FDPF8N50NZ N-Channel UniFETTM II MOSFET 500 V, 8 A, 850 m Ω

Features

- $R_{DS(on)}$ = 770 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 4 A
- · Low Gate Charge (Typ. 14 nC)
- Low C_{rss} (Typ. 5 pF)
- · 100% Avalanche Tested
- · Improve dv/dt Capability
- · ESD Improved Capability
- · RoHS Compliant

Applications

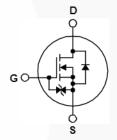
- · LCD/LED TV
- · Uninterruptible Power Supply
- Lighting
- · AC-DC Power Supply

Description

UniFETTM II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.







MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol		Parameter		FDP8N50NZ	FDPF8N50NZ	Unit	
V _{DSS}	Drain to Source Voltage	Drain to Source Voltage			500		
V _{GSS}	Gate to Source Voltage			±25		V	
	Drain Current	- Continuous (T _C = 25°C)		8	8*	۸	
ID	Drain Current	- Continuous (T _C = 100°C)		4.8	4.8*	_ A	
I _{DM}	Drain Current - Pulsed (Note 1)		32 32*		Α		
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)) 122		mJ	
I _{AR}	Avalanche Current		(Note 1)) 8		Α	
E _{AR}	Repetitive Avalanche Energy		(Note 1)) 13		mJ	
dv/dt	Peak Diode Recovery dv/	dt	(Note 3)	10		V/ns	
Б	Dawer Dissipation	(T _C = 25°C)		130	40.3	W	
P_D	Power Dissipation	- Derate above 25°C		1	0.3	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 t	o +150	°C		
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			3	300	°C	

^{*}Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FDP8N50NZ	FDPF8N50NZ	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.96	3.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	-0/00

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP8N50NZ	FDP8N50NZ	TO-220	Tube	N/A	50 units
FDPF8N50NZ	FDPF8N50NZ	TO-220F	Tube	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A$, $V_{GS} = 0 V$, $T_C = 25 ^{\circ} C$	500	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	-	0.5	-	V/°C
	Zero Gate Voltage Drain Current	V _{DS} = 500V, V _{GS} = 0V	-	-	1	
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 400V, T_{C} = 125^{\circ}C$	-	-	10	μА
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 25V, V_{DS} = 0V$	-	-	±10	μА

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu A$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10V, I _D = 4A	-	0.77	0.85	Ω
9FS	Forward Transconductance	V _{DS} = 20V, I _D = 4A	-	6.3	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	25)(1)(0)(-	565	735	pF
Coss	Output Capacitance	V _{DS} = 25V, V _{GS} = 0V f = 1MHz		-	80	105	pF
C _{rss}	Reverse Transfer Capacitance	1 - 11/11/12		-	5	8	pF
Q _{g(tot)}	Total Gate Charge at 10V			-	14	18	nC
Q _{gs}	Gate to Source Gate Charge	$V_{DS} = 400V, I_{D} = 8A$ $V_{GS} = 10V$		-	4	-	nC
Q _{gd}	Gate to Drain "Miller" Charge	V _{GS} = 10V		-	6	-	nC

Switching Characteristics

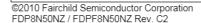
t _{d(on)}	Turn-On Delay Time		-	17	45	ns
t _r	Turn-On Rise Time	$V_{DD} = 250V, I_D = 8A$	-	34	80	ns
t _{d(off)}	Turn-Off Delay Time	$R_G = 25\Omega$, $V_{GS} = 10V$	-	43	95	ns
t _f	Turn-Off Fall Time	(Note 4)	-	27	60	ns

Drain-Source Diode Characteristics

Is	Maximum Continuous Drain to Source Diode Forward Current		-	-	8	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	30	А
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 8A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _{SD} = 8A	-	228	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	-	1.43	-	μС

Notes

- Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 3.8mH, I_{AS} = 8A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25°C
- 3. I $_{SD} \leq$ 8A, di/dt \leq 200A/µs, V $_{DD} \leq$ BV $_{DSS}, \ Starting \ T_J$ = 25°C
- 4. Essentially Independent of Operating Temperature Typical Characteristics



Typical Characteristics

Figure 1. On-Region Characteristics

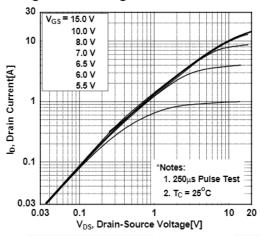


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

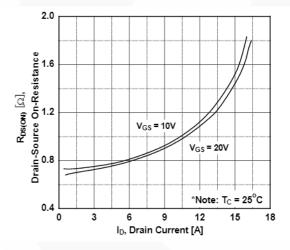


Figure 5. Capacitance Characteristics

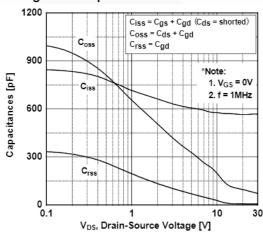


Figure 2. Transfer Characteristics

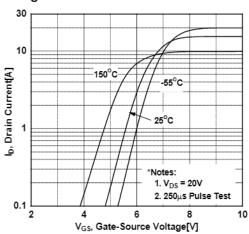


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

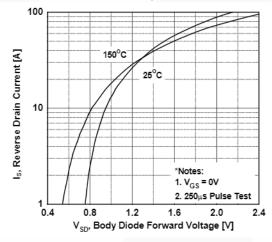
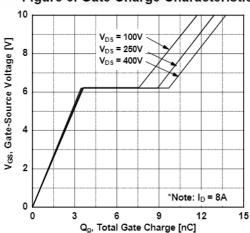
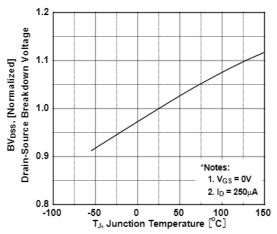


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature



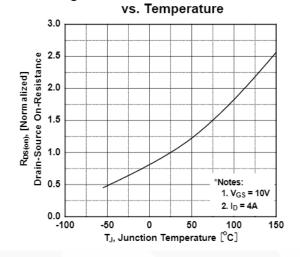


Figure 8. On-Resistance Variation

Figure 9. Maximum Safe Operating Area - FDP8N50NZ

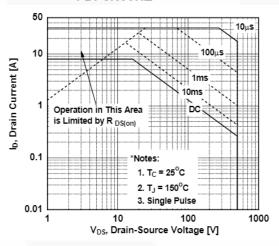


Figure 10. Maximum Safe Operating Area - FDPF8N50NZ

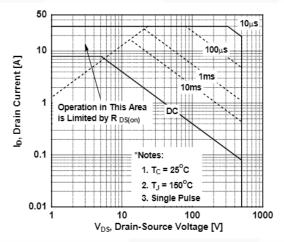


Figure 11. Maximum Drain Current vs. Case Temperature

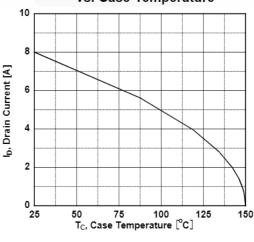
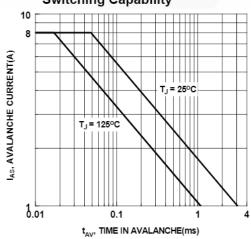


Figure 12. Unclamped Inductive Switching Capability



Typical Characteristics (Continued)

Figure 13. Transient Thermal Response Curve - FDP8N50NZ

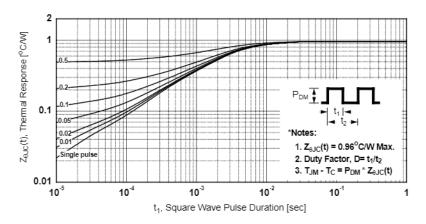


Figure 14. Transient Thermal Response Curve - FDPF8N50NZ

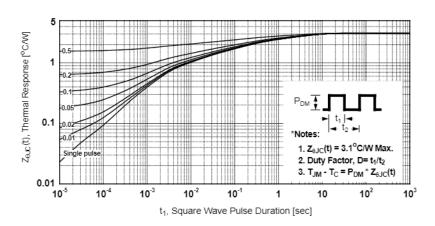


Figure 15. Gate Charge Test Circuit & Waveform

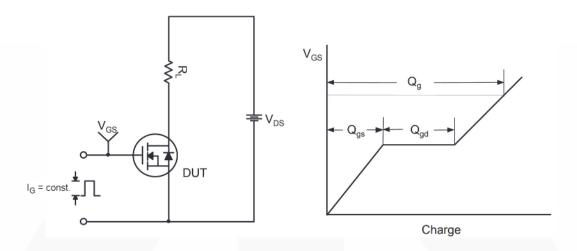


Figure 16. Resistive Switching Test Circuit & Waveforms

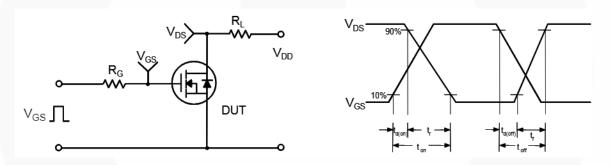
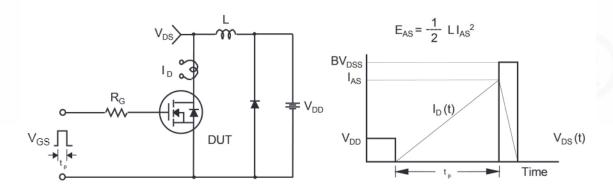


Figure 17. Unclamped Inductive Switching Test Circuit & Waveforms



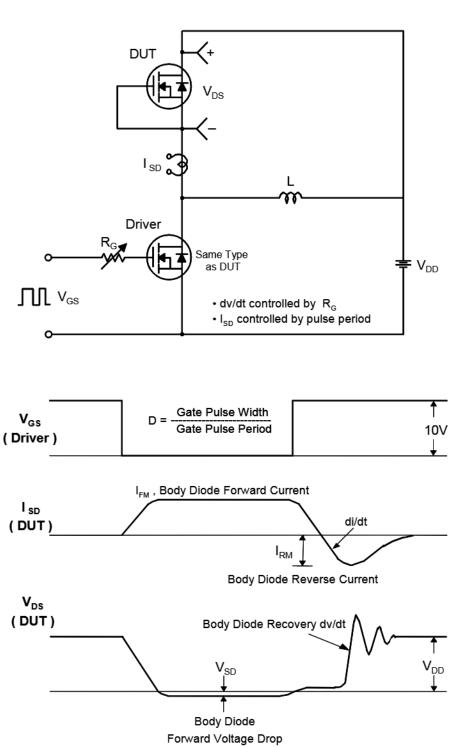


Figure 18. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

TO-220 3L

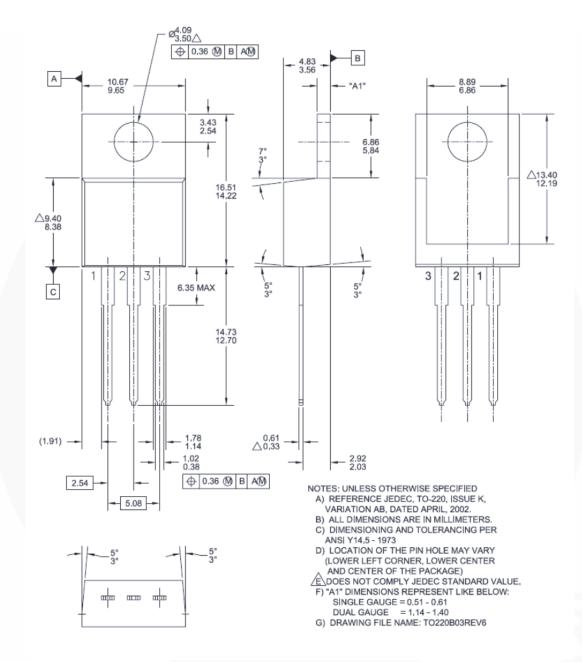


Figure 19. TO-220, Molded, 3Lead, Jedec Variation AB

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Dimension in Millimeters

Mechanical Dimensions

TO-220F 3L

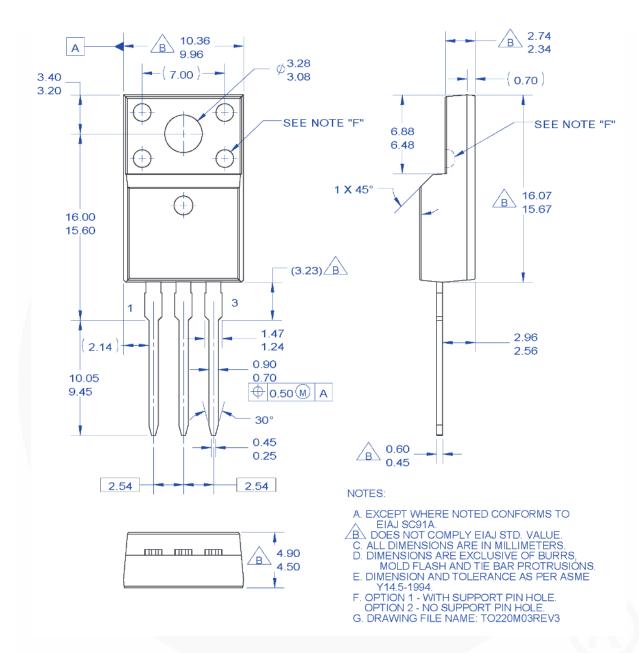


Figure 20. TO220, Molded, 3LD, Full Pack, EIAJ SC91, Straight Lead

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Dimension in Millimeters





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